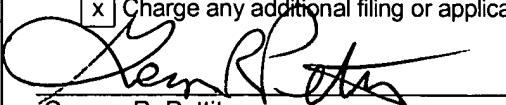


AF 12822



NOV 25 2002

AMENDMENT TRANSMITTAL LETTER				Docket No. 21776-00039-US	
Application No. 09/387,857-Conf. #3099	Filing Date September 1, 1999	Examiner C. Novacek		Art Unit 2822	
Applicant(s): Fumitaka Sugaya					
Invention: A SEMICONDUCTOR DEVICE AND A METHOD OF MANUFACTURING THE SAME					
TO THE COMMISSIONER FOR PATENTS					
Transmitted herewith is an amendment in the above-identified application.					
The fee has been calculated and is transmitted as shown below.					
CLAIMS AS AMENDED					
Total Claims	18	- 20 =	0	x	0.00
Independent Claims	5	- 5 =	0	x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT: 0.00					
<input checked="" type="checkbox"/> Large Entity			<input type="checkbox"/> Small Entity		
<input type="checkbox"/> No additional fee is required for this amendment.					
<input type="checkbox"/> Please charge Deposit Account No. 22-0185 in the amount of \$. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge and credit Deposit Account No. 22-0185 as described below. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 George R. Pettit Attorney Reg. No.: 27,369 CONNOLLY BOVE LODGE & HUTZ, LLP 1990 M Street, N.W., Suite 800 Washington, DC 20036-3425 (202) 331-7111					
Dated: 11-25-02					
NOV 29 2002 TECHNOLOGY CENTER 2800					
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Docket No.: 21776-00039-US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Conf. No. 3099

Fumitaka Sugaya

Application No.: 09/387,857

Group Art Unit: 2822

Filed: September 1, 1999

Examiner: C. Novacek

For: A SEMICONDUCTOR DEVICE AND A
METHOD OF MANUFACTURING THE
SAME

Amendment
11/10 12/3/02
A. Wells
1/23/03

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NOV 29 2002

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AMENDMENT UNDER 37 CFR 1.116

Box AF

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Final Rejection mailed August 23, 2002 (Paper No. 10), please amend the above-identified U.S. patent application as follows:

IN THE CLAIMS:

Kindly amend the claims as follows:

32. (Amended) A method of fabricating a semiconductor device, comprising:
the first step of defining an element active region by forming an element isolation structure on a semiconductor substrate;
the second step of forming a gate insulating film and a gate electrode in said element active region;
the third step of doping an impurity into said active region of said substrate to form a pair of impurity diffusion layers in surface regions of said semiconductor substrate on two sides of said gate electrode;